



Universität Hamburg

DER FORSCHUNG | DER LEHRE | DER BILDUNG

PAUL SCHERRER INSTITUT



Project P2: Hybrid Pixel Detectors Jennifer Sibille (ESR)

Paul Scherrer Institut, Villigen, CH

Supervisor: Dr. Tilman Rohe

Thesis Advisor: Prof. Alice Bean

MC-PAD Closing Event

19-22 September, 2012

Laboratori Nazionali di Frascati, INFN

- Biography
- Introduction
 - Project P2: Hybrid Pixel Detectors
 - CMS pixel detector
 - Radiation effects on detector operation
- Research Work
 - Charge collection efficiency measurement
 - Interpixel capacitance
 - Charge as a function of position within a pixel
 - Single-sided sensors
 - Conclusions
- Present Status
- Evaluation of MC-PAD ITN

Start date: 01 April, 2009
End date: 31 March, 2012
Home Country: USA

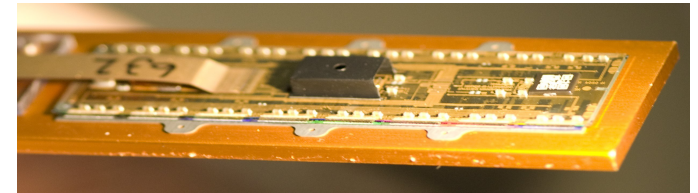
Education Background:

- BS in Physics and Mathematics, May 2006
 - Louisiana Tech University, Ruston, LA, USA
- MS in Physics, December 2008
 - University of Kansas, Lawrence, KS, USA
 - “Charge Collection Efficiency Measurement of CMS Pixel Detector”

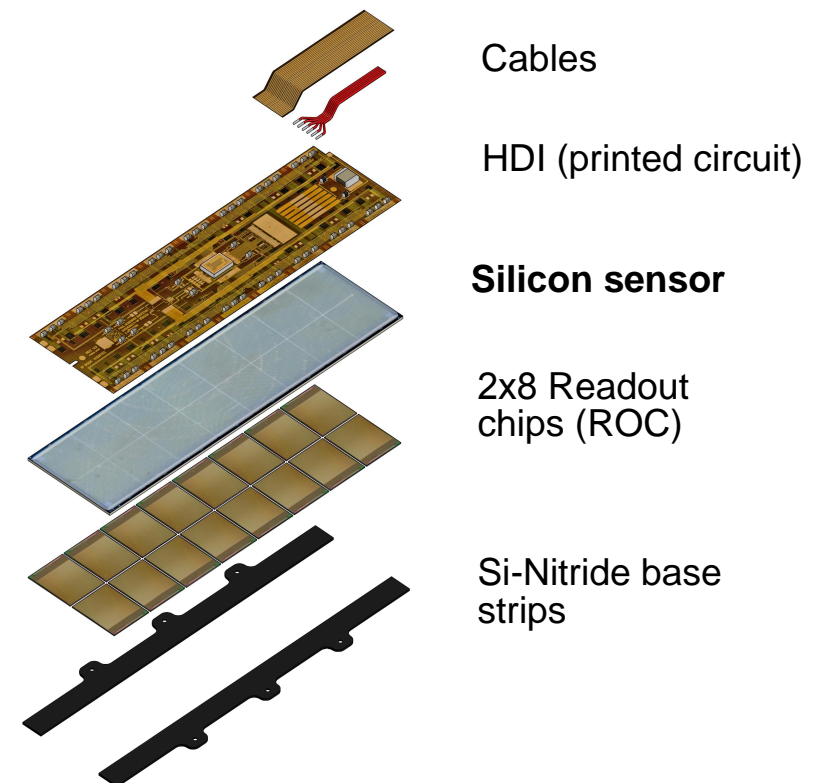
Details of ESR Position:

- Institute: Paul Scherrer Institut (PSI), Villigen, CH
- Project: P2 Hybrid Pixel Detectors
- Supervisor: Dr. Tilman Rohe
- PhD Thesis: “Radiation Hard Hybrid Pixel Detectors, and a $b\bar{b}$ Cross-Section Measurement at the CMS Experiment”
 - Thesis advisor: Prof. Alice Bean
 - University of Kansas, Lawrence, KS, USA

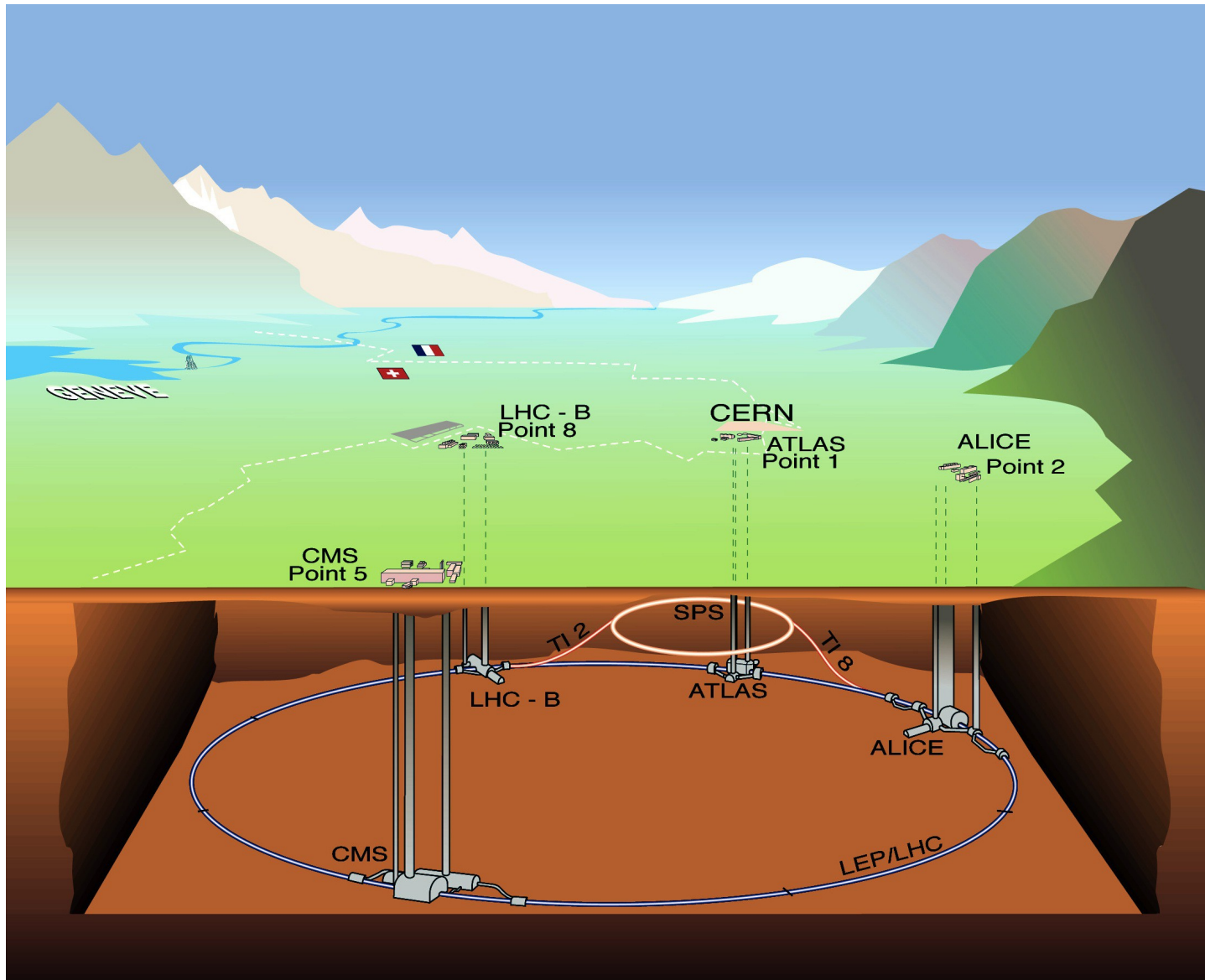
- Motivation: Tracking detectors at LHC and X-FEL are exposed to large radiation doses which degrade performance after a few years
- Project Focus: Cost-effective and radiation-hard hybrid pixel detectors using standard components
- First step is to understand operational limit of current detectors
- Measurements and simulations of the degradation of sensors as a function of integrated fluence



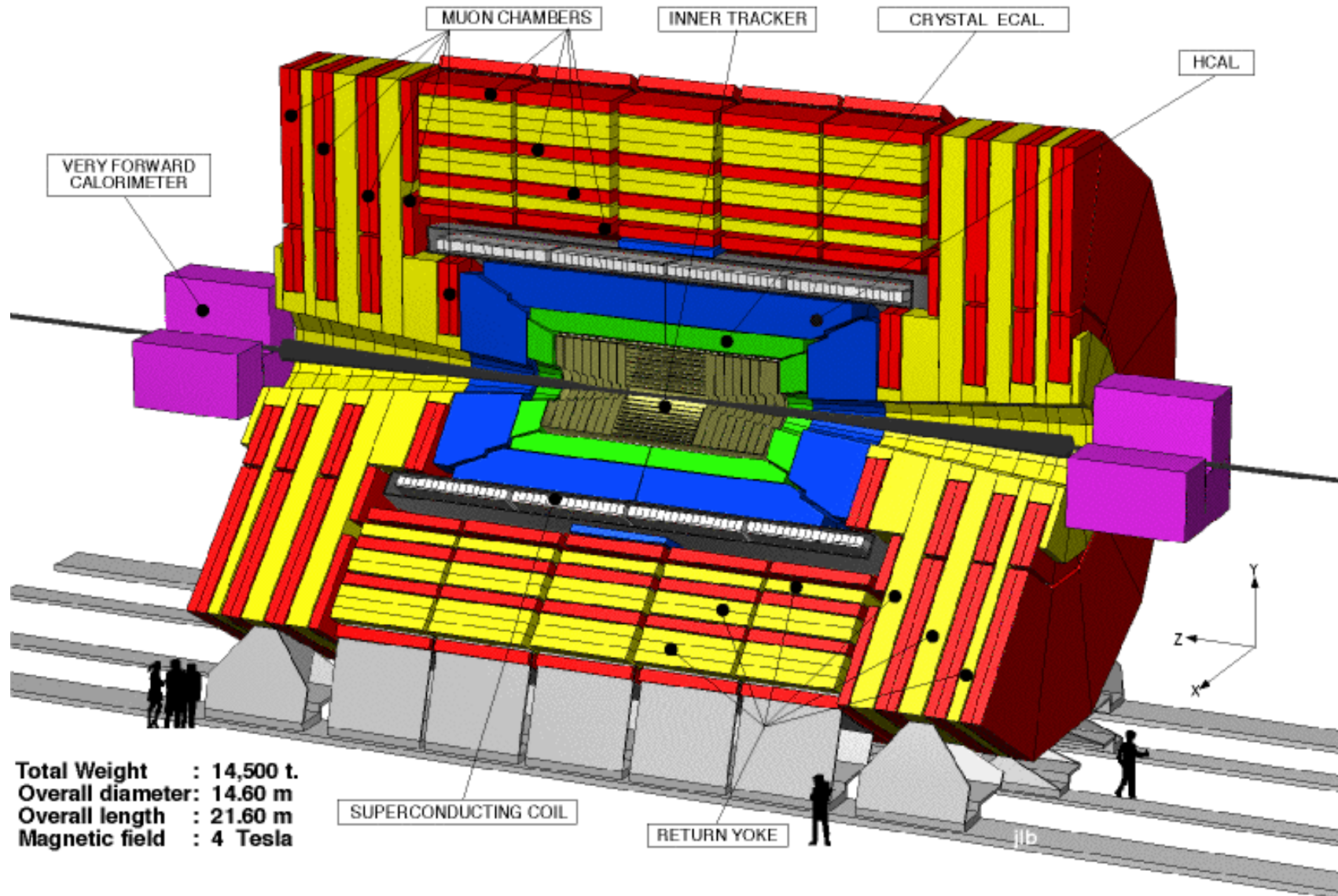
CMS barrel pixel module



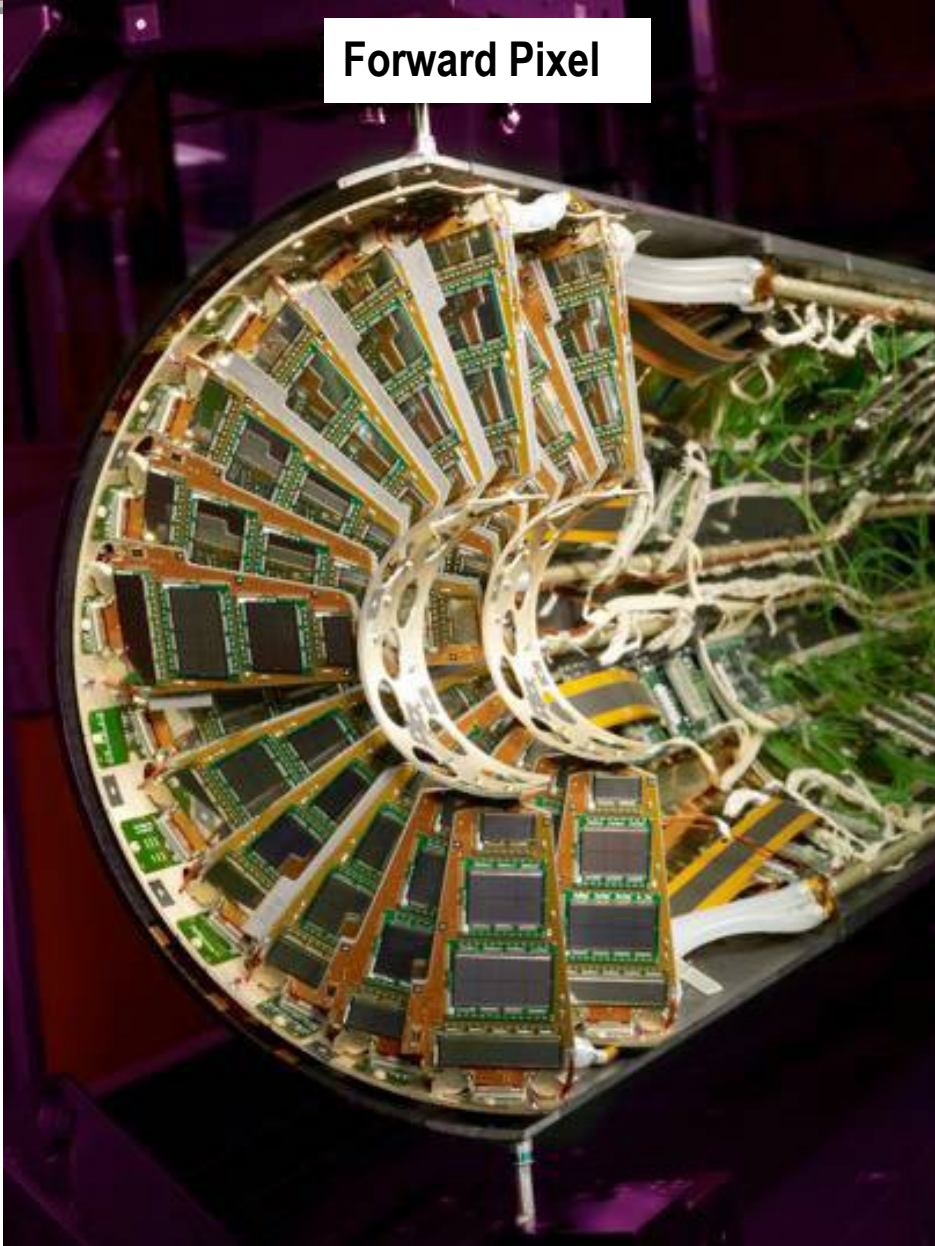
Large Hadron Collider



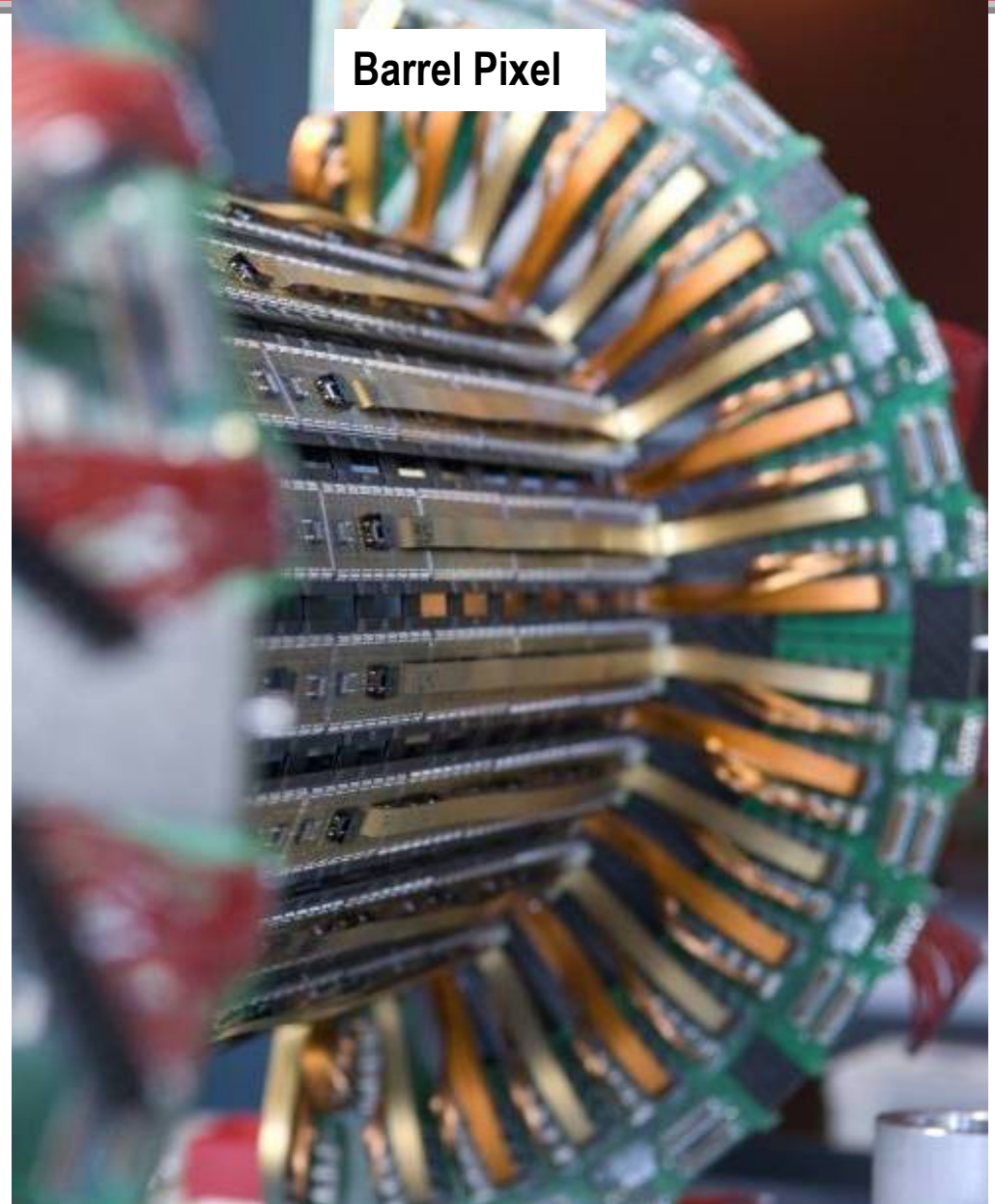
The CMS Detector

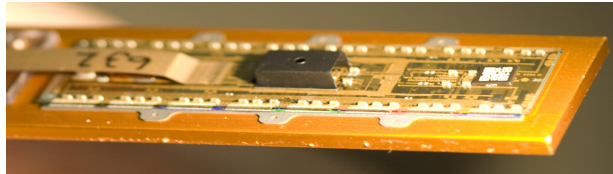


Forward Pixel



Barrel Pixel





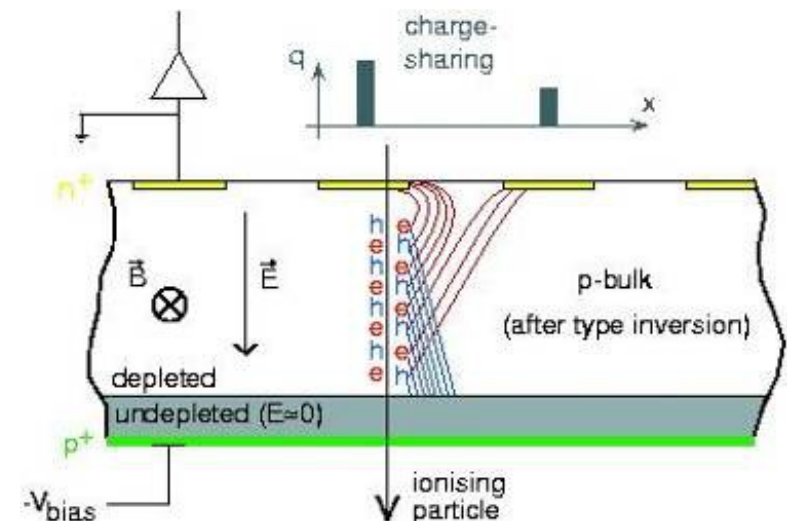
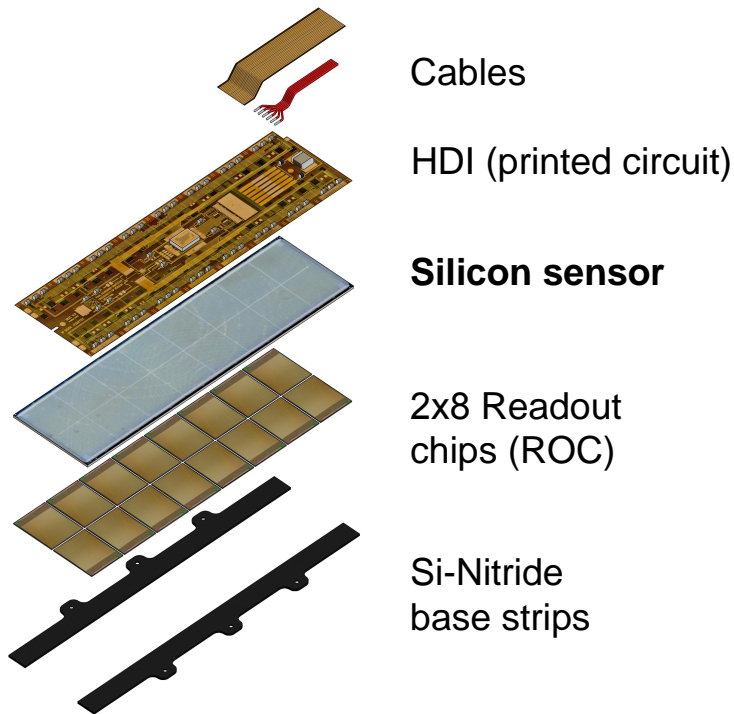
CMS barrel pixel module

Pixel detector:

- High granularity, good spatial resolution
 - vertexing
- Close to interaction point, subjected to large radiation dose

Magnetic field:

- Charges in sensor experience Lorentz force
- Better spatial resolution due to charge sharing between pixels



Particles passing through the sensor cause radiation damage!

For layer at 3 cm from interaction point, $\sqrt{s} = 14$ TeV:

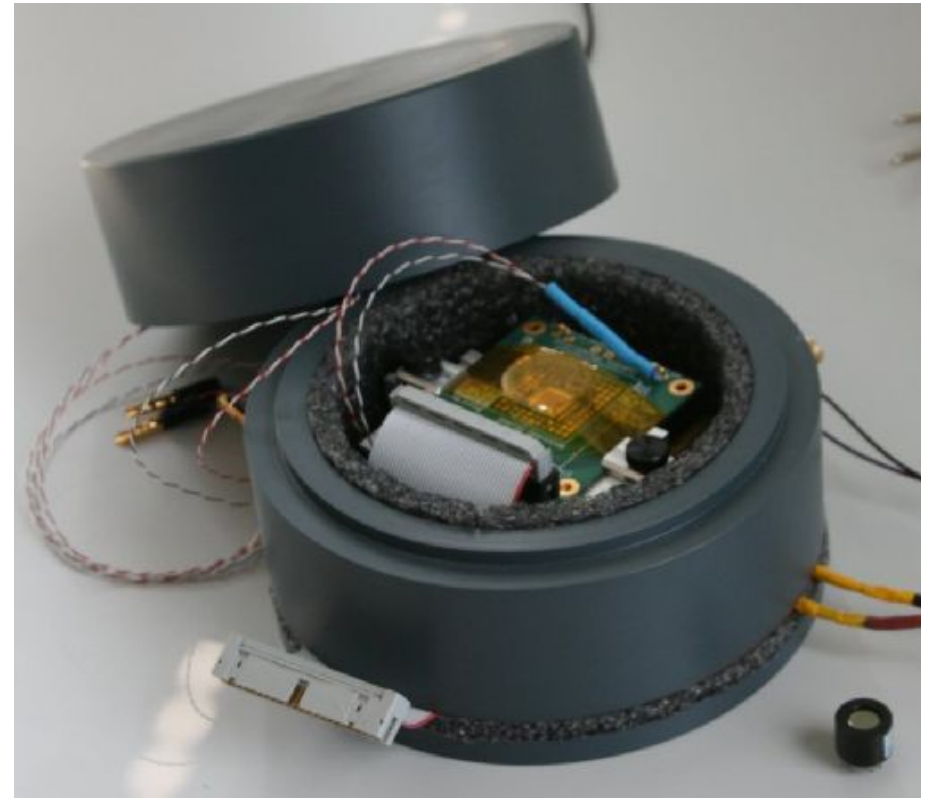
$\Phi < \sim 1.5 \times 10^{15} n_{eq}/\text{cm}^2$ ($\int L dt < \sim 250 \text{ fb}^{-1}$):

- Bias voltage has to be increased
- Spatial resolution degrades
- Cooling necessary to limit leakage current, reverse annealing

$\Phi > \sim 1.5 \times 10^{15} n_{eq}/\text{cm}^2$ ($\int L dt > \sim 250 \text{ fb}^{-1}$):

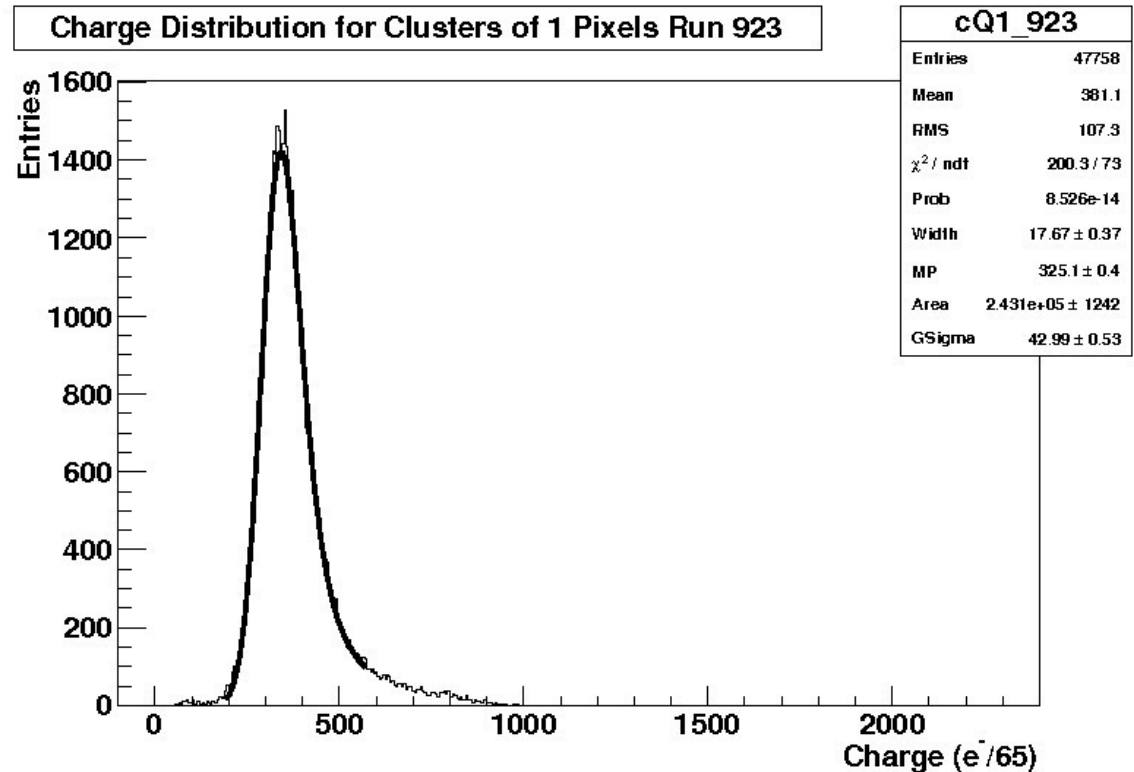
- Charge trapping leads to reduced signal and loss in efficiency
- Recent measurements (e.g. University of Hamburg, University of Liverpool, University of Freiburg) show that measured signal is higher than expected if bias voltage can be increased to values $\gg 600$ V
- Connectors, cables and power supplies in CMS only qualified to 600 V
- Leakage current rising proportional with Φ becomes significant fraction of the power load (cooling)

- Samples irradiated up to fluence of $5 \times 10^{15} \text{ n}_{\text{eq}} / \text{cm}^2$
 - Pions (300 MeV) at PSI Pi-E1 up to $\sim 6 \times 10^{14} \text{ n}_{\text{eq}} / \text{cm}^2$ ($> 10^{15} \text{ n}_{\text{eq}} / \text{cm}^2$ Aug 2010)
 - Protons (21 GeV) at CERN-PS up to $\sim 5 \times 10^{15} \text{ n}_{\text{eq}} / \text{cm}^2$
 - Protons (24 MeV) at Karlsruhe up to $\sim 5 \times 10^{15} \text{ n}_{\text{eq}} / \text{cm}^2$
- ^{90}Sr source for measurement
- Samples tested at -20°C
- No independent trigger, so no efficiency measurement with this setup

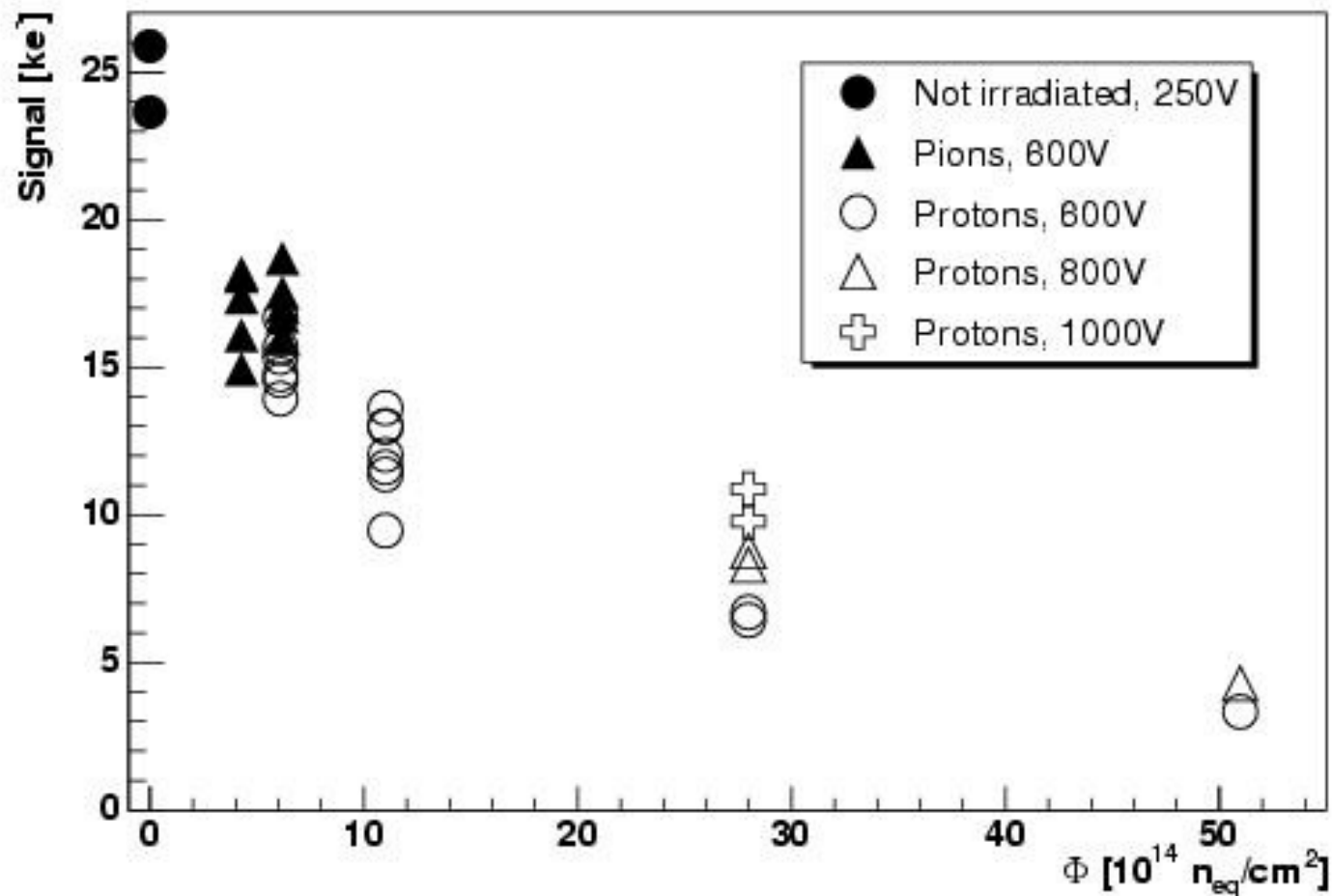


Cold box for testing irradiated samples

- Charge deposited by a charged particle passing through silicon is Landau distribution
- “Signal” is defined as the most probable value of charge distribution



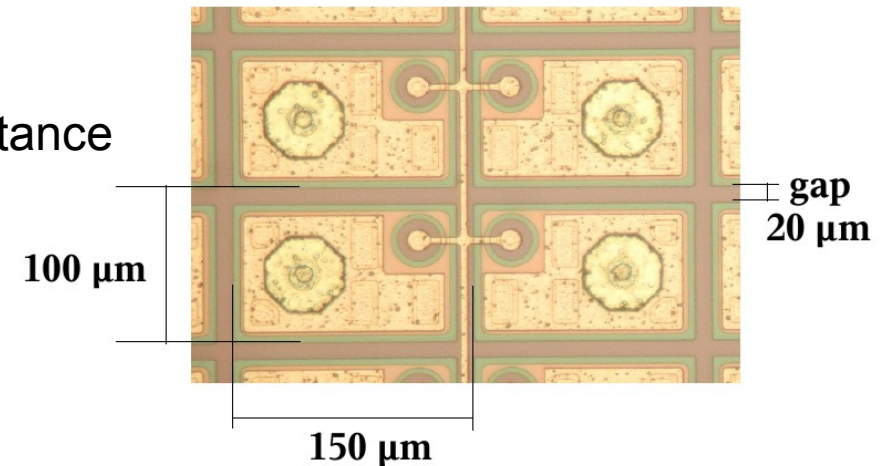
CCE Results



Collected charge vs. fluence

- Can still get significant charge (with high bias) up to $\sim 3e15 n_{eq}/cm^2$
 - Results for $5e15 n_{eq}/cm^2$ inconclusive
 - No sign of saturation of signal at $3e15 n_{eq}/cm^2$
- However:
 - Cables in CMS only qualified for 600 V
 - Couldn't go to higher bias
 - Problems with sparking on PCB, humidity, connectors
 - Redesigned PCBs so this is possible in future

- Capacitance leads to cross-talk, degrades resolution
- Small gap: more uniform drift field, but higher capacitance
- Trade-off between low capacitance and small gap
- Current pixels have 20 μm gap
- Want to see if increasing gap size is beneficial

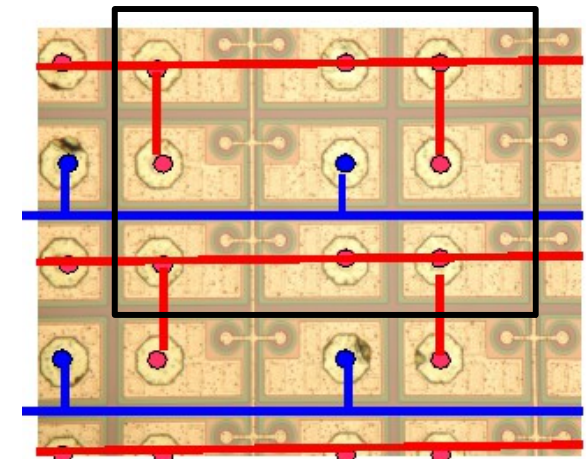


- Designed a “readout chip replacement” – simple chip to connect groups of pixels together
 - Groups connected together and routed to pads on periphery
 - Only 2 pads which can be contacted by needles

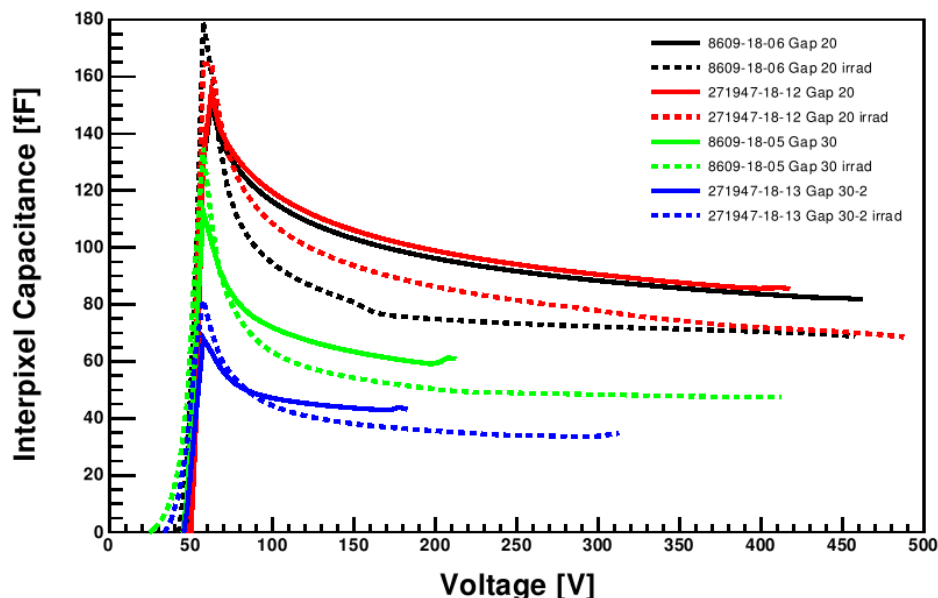
Measured sensors with different gap sizes and geometries

Irradiated some sensors with ^{60}Co

1 pixel (blue) surrounded by 8 neighbors (red)

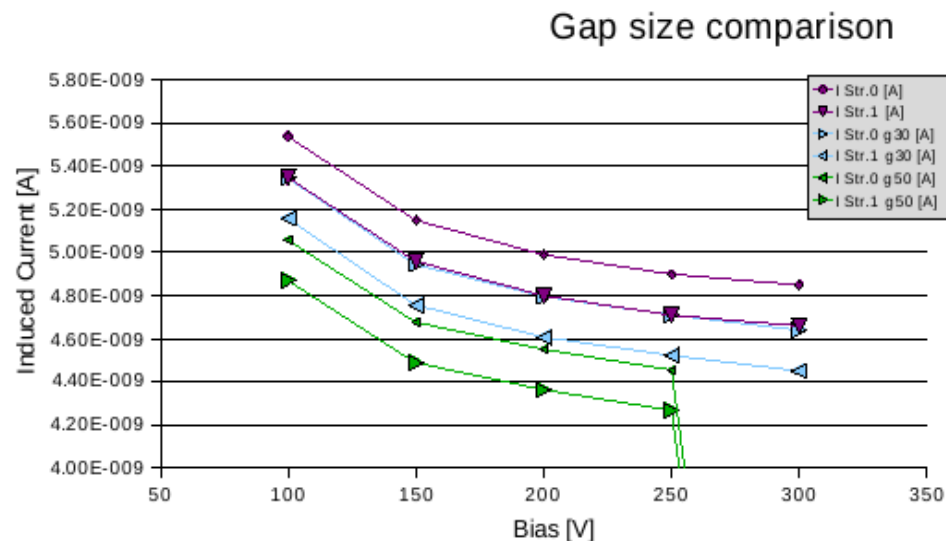


Measurements



Black/Red: 20 μm Solid: Unirradiated
 Blue/Green: 30 μm Dashed: Irradiated

Simulations



Purple: 20 μm Blue: 30 μm Green: 50 μm

NB: Pixels are not isolated before full depletion (ignore everything before 50 V)

Qualitative agreement between simulations and measurements – no quantitative comparison

Capacitance decreases with increasing bias voltage – possible depletion of p-spray

Capacitance decreases with irradiation

Planned to measure other devices (open p-stop, 3D), unable to obtain samples until Summer 2012

- Plan to publish results

- As exchange with project partner, I went to the University of Hamburg in December 2010 for a small project
- Irradiated some sensors (with ROC) in the DORIS F4 beamline (~1 MGy)
- Induce charge in a very localized area using red laser
- Questions:
 - Are there areas of the pixel which have lower charge collection?
 - How does this change with irradiation?
- Made 2D scan over pixel, starting outside edges of pixel
- Laser spot width ~5 μm
- Steps of 10 μm
 - Unfortunately we ran out of time so were unable to do a finer scan
- Unable to operate irradiated readout chips
- Charge collection fairly homogenous, reproducible – nothing unexpected

Many thanks to Jiaguo Zhang and Thomas Pöhlsen for their help!

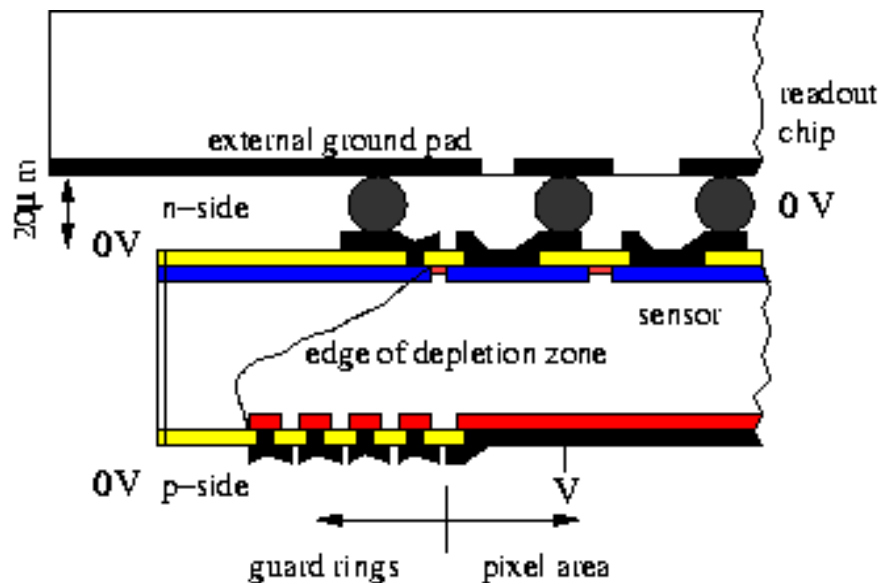
Apart from bump-bonding, sensors are most expensive part of detector -> try to reduce costs

Single-sided processing cheaper (factor 2-3!)

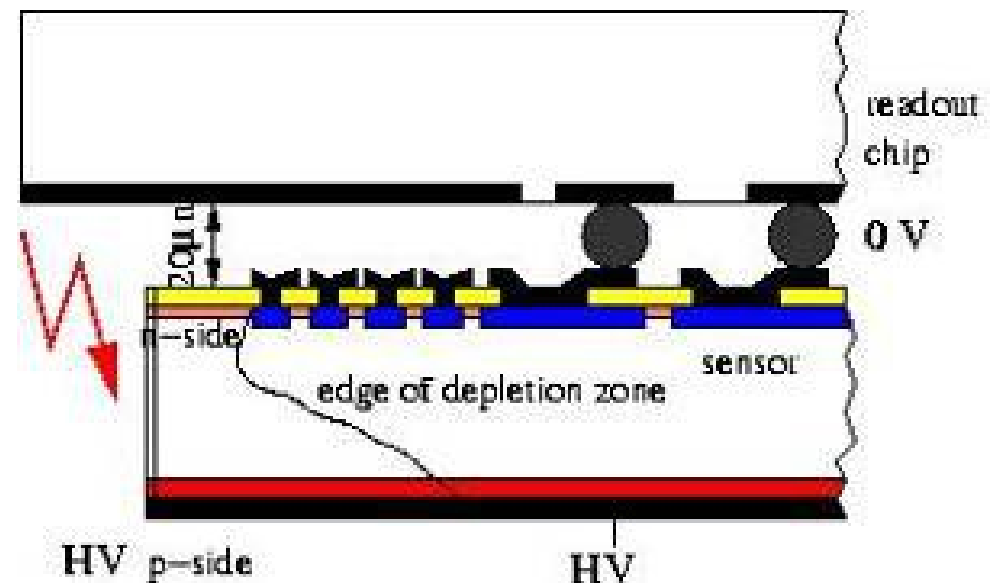
BUT edges of chip remain at high voltage in single-sided sensors

- Risk of sparking to readout chip (ground)

Need a cheap and reliable method to prevent this problem in order to be feasible



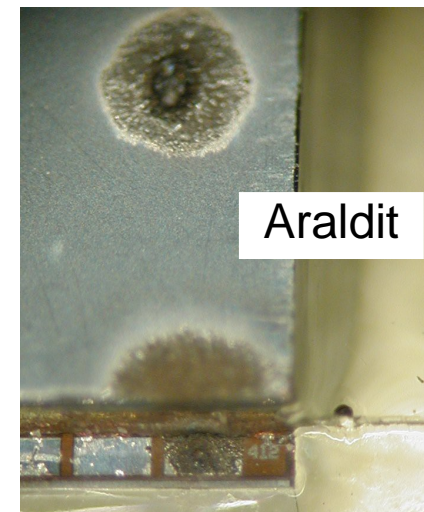
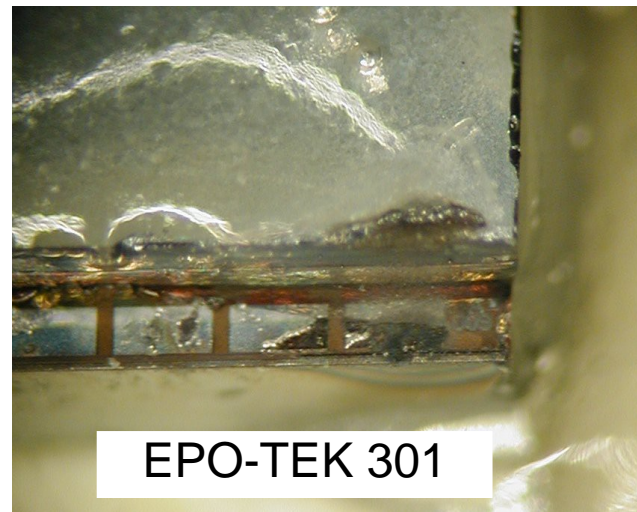
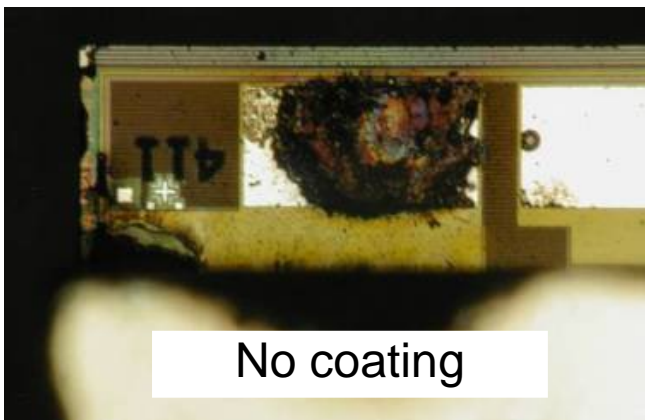
Double-sided



Single-sided

Maybe can cover edges with another material to prevent sparking?

- Tried two different glues (Araldit and EPO-TEK 301) without success
- Sparks at 500-700 V



Coated with polymer (Paralyene C) with chemical vapor deposition process

- Standard industrial procedure
- Held at 1000 V for several hours with no sparks
- **Possible solution** to be investigated further, has problems to be solved
 - Wire bond pads should not be covered

- **Charge Collection Efficiency**
 - Can get significant charge (with high bias) up to $\sim 3e15 n_{eq}/cm^2$
- **Interpixel Capacitance**
 - Capacitance decreases with larger gap size
 - Finally decided to keep same gap size for upgrade
- **Single-Sided Sensors**
 - Coating sensors with glue has no effect on sparking
 - Problem may be solved by coating with polymer
- In the end, measurements helped to show that the current sensors are still suitable for Phase 1 upgrade

- Finishing thesis, PhD expected by end of the year
- Postdoc position at University of Hamburg (16.05.2012)
- Working on the CMS pixel phase 1 upgrade
- Production and testing of 350 barrel pixel modules
 - Build up module assembly stations
 - Build setup for testing/calibrating modules with x-rays

Positive aspects:

- Training events were a great opportunity to learn about other research areas and meet people from other institutes
 - I found the event on CV writing and interviewing especially helpful
 - Build a relationship with other people, which you don't get from summer schools, etc
- Exchange with project partner also interesting
 - Chance to work with another group

Negative aspects:

- Would have liked more participation from the industry partners
- So many travel opportunities sometimes made it difficult to balance work in the lab and travel

MC-PAD ITN was a great experience, and I would definitely recommend it!

Thank you for the wonderful opportunity!

PUBLICATIONS AND PRESENTATIONS

“Radiation hardness of CMS pixel barrel modules.” Rohe, T. et al. Nucl.Instrum.Meth. A624 (2010) 414-418.

“Signal height in silicon pixel detectors irradiated with pions and protons”. Rohe, T. et al. Nucl.Instrum.Meth. A612 (2010) 493-496.

XI ICFA School on Instrumentation in Elementary Particle Physics, San Carlos de Bariloche, Argentina, January 2010

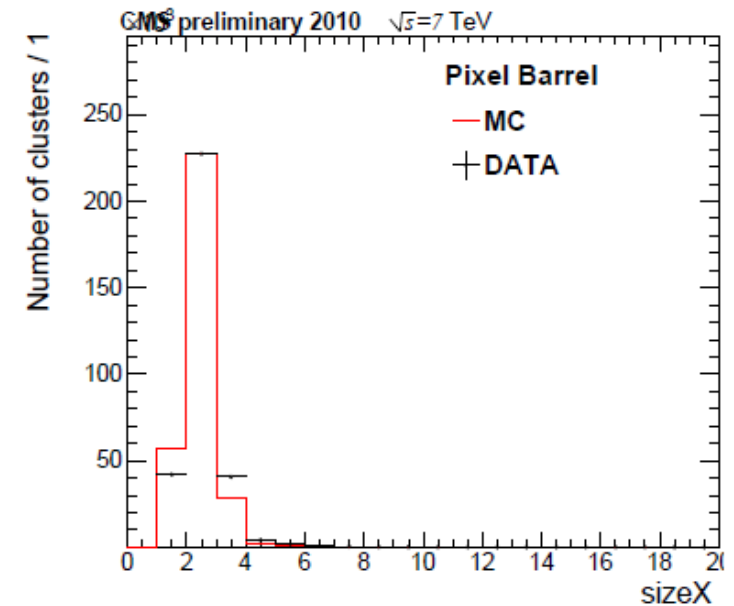
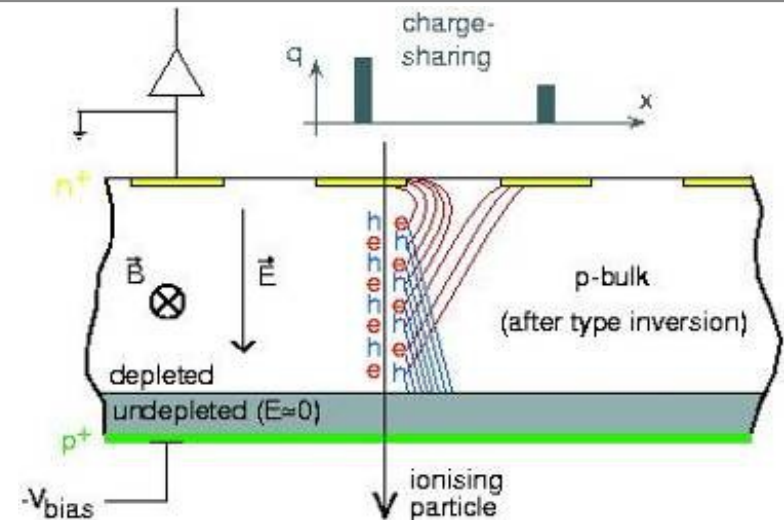
- Presented poster: “Design of CMS Pixels for an LHC Upgrade”

14th RD50 Workshop, Freiburg, Germany, June 2009

- Presentation: "Sensor R&D for an upgrade of the CMS pixel barrel"

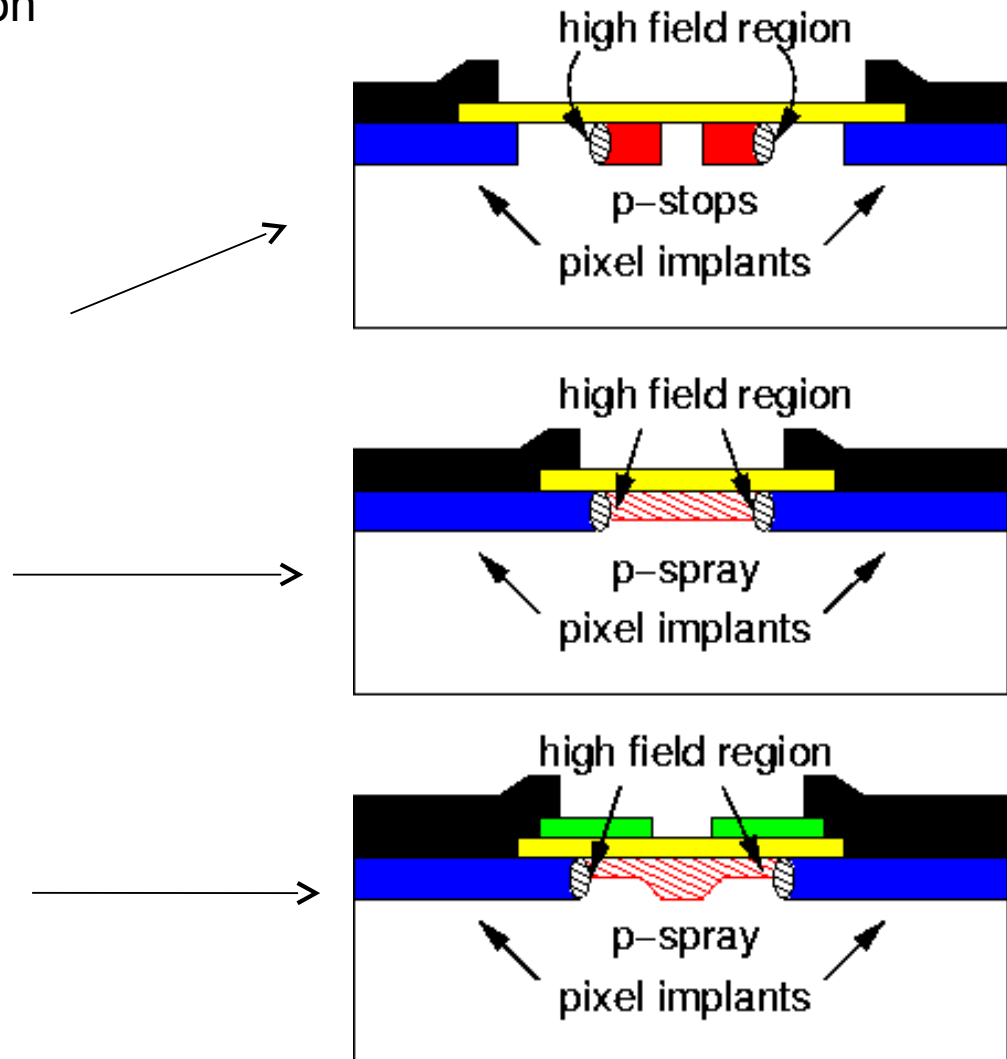
Back-up Slides

- Present CMS-pixel detector displays good spatial resolution ($\sim 13 \mu\text{m}$)
- High fraction of 2-pixel clusters
 - High magnetic field (3.8 T)
 - High mobility of electrons
 - Low bias voltage (150 V in the barrel)
- Interpolation techniques in 2-pixel clusters
- Cumulative radiation damage requires increase of bias voltage
- High electric field reduces mobility of charge carriers
- Lorentz angle is also reduced
- Fraction of double hits is reduced
- Resolution slowly degrades up to the binary value (pitch/sqrt(12) $\sim 30 \mu\text{m}$ with current pitch)
- Process is slow and steady
- Detector might become “useless” for impact parameter measurement although detection efficiency is still high ($>95\%$)

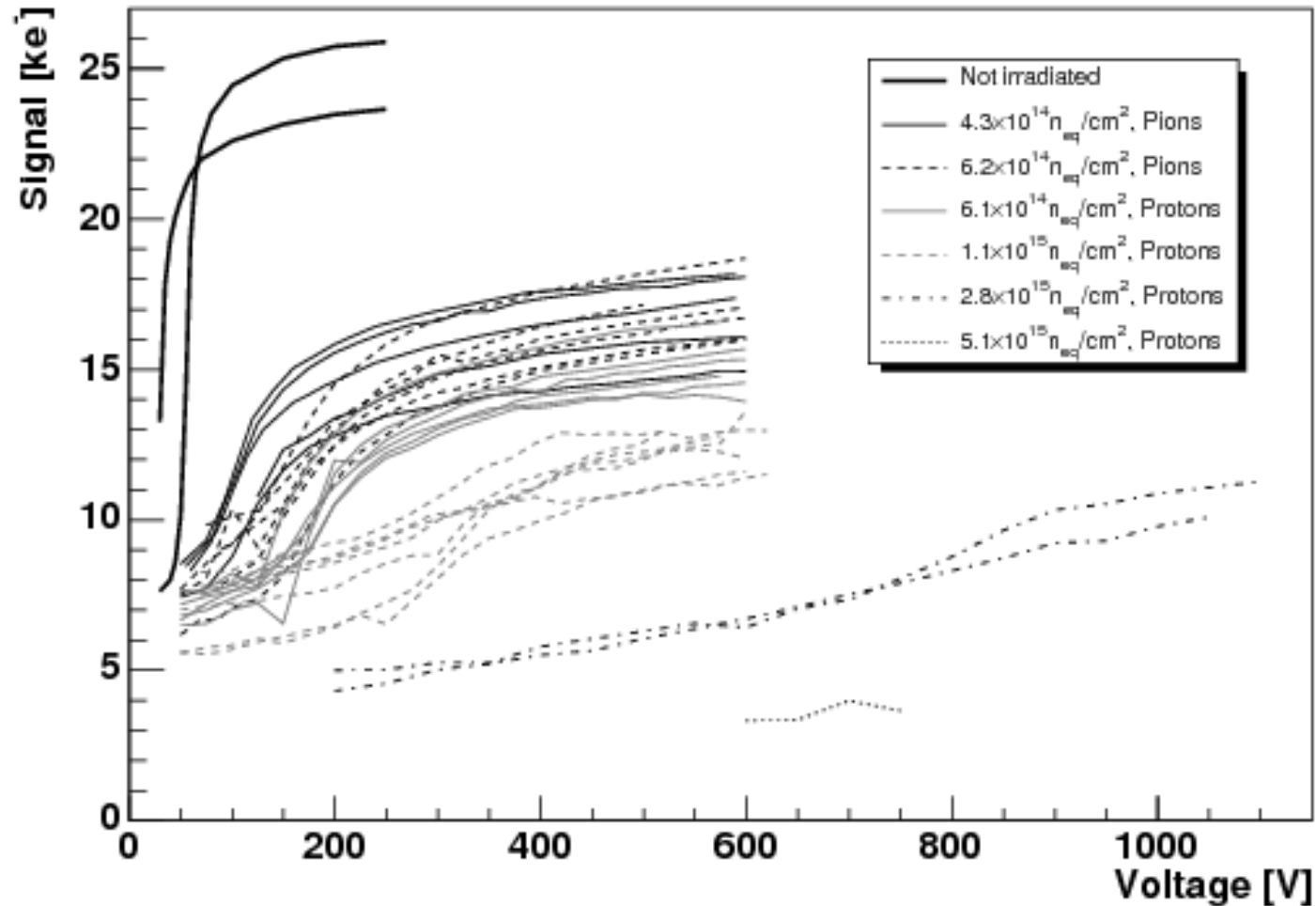


Distribution of cluster size (in $r\phi$)

- In n⁺-in-n sensors, electron accumulation layer would short out implants without some sort of isolation (p-type implant)
- p-stop: high dose p-implant between n⁺ implants
 - Requires extra photolithographic step
- p-spray: medium dose boron implant uniformly over surface
 - No extra photolithographic step
- **moderated p-spray**: p-spray process performed later in the process, any structures are reproduced in the doping profile
 - Can use higher dose to ensure sufficient isolation, no breakdown

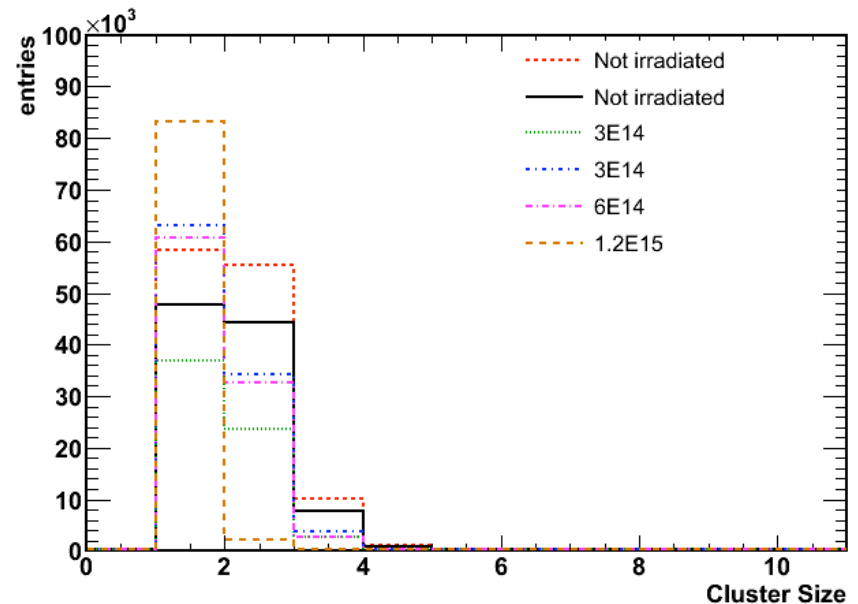
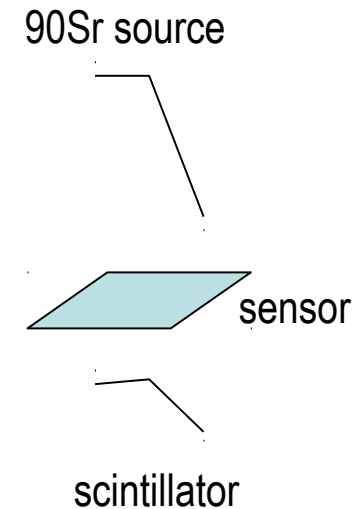


CCE Results



Collected charge vs. bias voltage for samples irradiated to different fluences

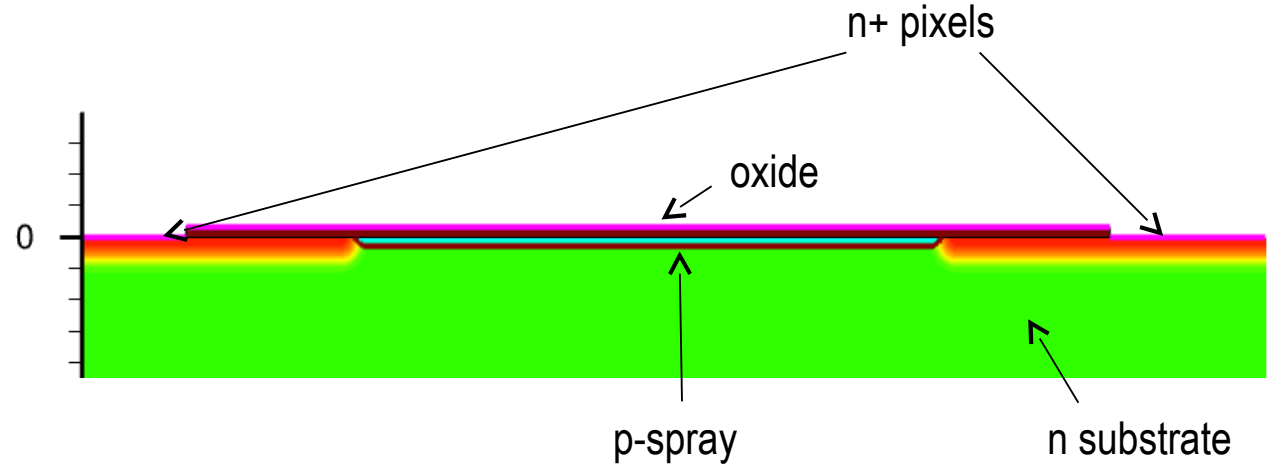
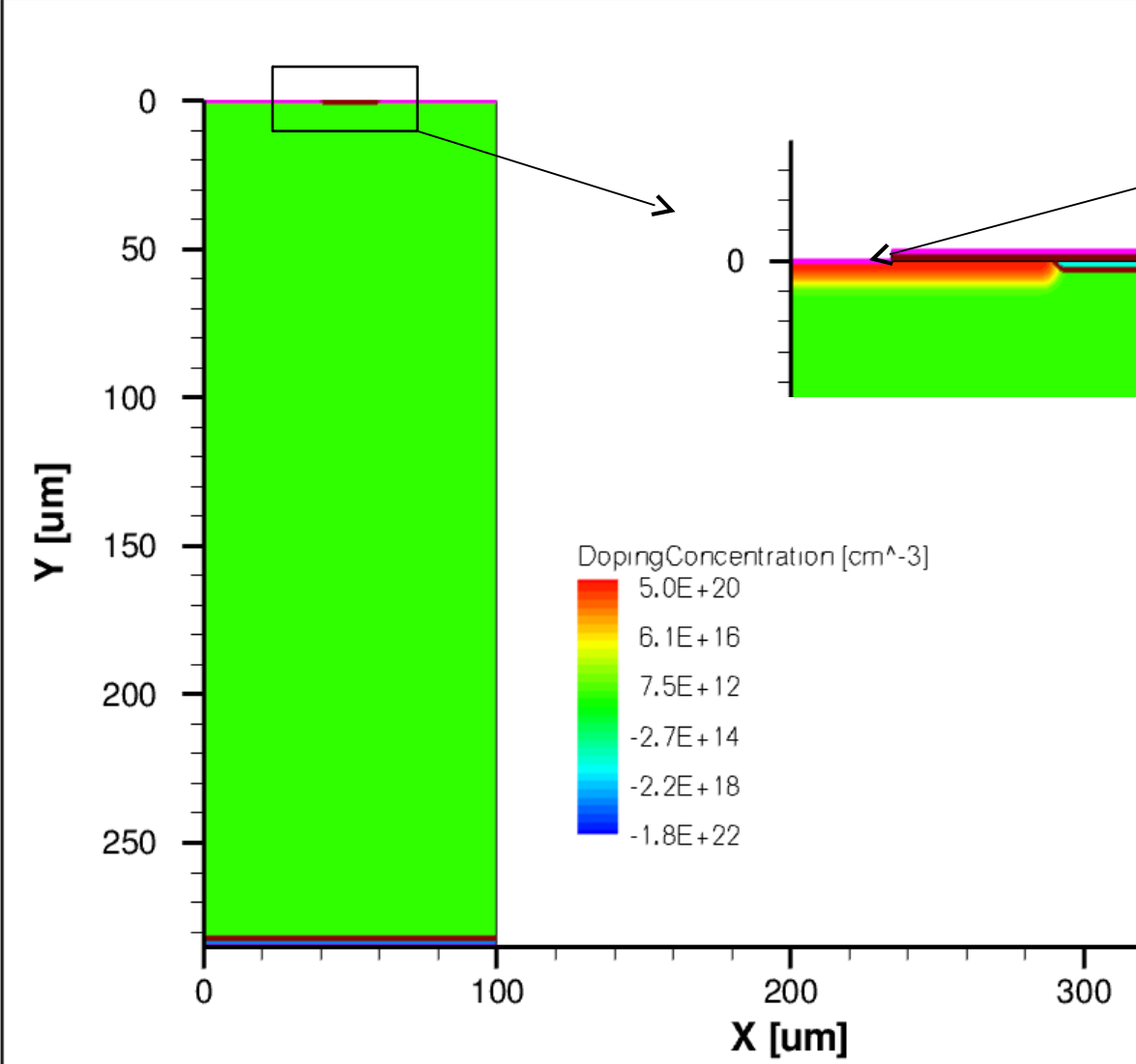
- CCE setup was upgraded to include a scintillator and photomultiplier tube – independent trigger
- Wanted to make detection efficiency measurements
- Reflections and geometry artificially lower the efficiency, so unable to make absolute efficiency measurements
- Measurements were performed by Joaquin Siado (Master's student from University of Puerto Rico Mayaguez) as part of the PIRE program*
 - New CCE results agree with previous measurement
 - Setup changes also introduce an energy cut, reduces tail of large clusters – better data quality



* PIRE program funded by US National Science Foundation

Interpixel Capacitance - Simulation

1: n-in-n_simple_msh.tdr 0-0



- Simple 2D Synopsys TCAD simulation
- Vary gap size (20, 30, 50 μm)

- When close to pixel border, some charge collected by neighboring pixel(s)
- Pulse height distribution for charge near pixel edges shows clearly multiple peaks
 - 2, 3, or 4 based on position
- Charges are added together to get “cluster charge”

